

AMENDMENTS TO THE SPECIFICATION

Please replace the present title with the following amended title:

A p-Type ZnS Based Semiconductor Material having a Low Resistance Due to its High Copper Content and Semiconductor device using the Same

Please replace the paragraph no. [0009] with the following amended paragraph:

Patent Document 1: JP Patent No. 3078611 (Patentee Minnesota Mining & Manufacturing, University of Florida), also published as JP 4-234136.

Non-Patent Document 1 : Journal of Crystal Growth, vol. 197(1999), pp. 557-564/W.

Faschinger.

Non-Patent Document 2: Journal of Crystal Growth, vol. 214/215(2000), pp. 1064-70/A.

Katayama et al.

Non-Patent Document 3: Optophysical Property Handbook (Asakura Bookstore, 1984) pp. 182-185.

Please replace the paragraph no. [0024] with the following amended paragraph:

In the semiconductor material according to the invention, furthermore, a carrier concentration of the semiconductor material is equal to or higher than 10^{16} ~~10^{15}~~ cm^{-3} and is lower than 10^{22}cm^{-3} .

By this structure, the semiconductor material can be effectively applied, as a p-type semiconductor or a hole injecting electrode layer, to a semiconductor device.